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REMARKS

Upon entry of the foregoing amendments, claims 1-8 and 14-27 are pending.

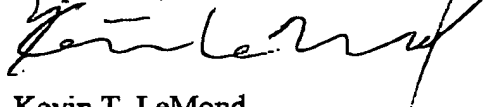
Applicants submitted an amendment on June 7, 2002, which was responsive to the office action mailed December 13, 2001. This response was resubmitted to the USPTO on August 12, 2002 via facsimile. On November 5, 2002, a communication was issued indicating that the amendment to the claims was not entered because the amendment to the claims should be made in accordance with 37 CFR §1.121(a)(2)(ii). Accordingly, applicant is resubmitting the claim amendments with this response. It is respectfully requested that the two amended drawing sheets submitted on June 7, 2002 be considered by the Examiner, along with the remarks contained within that response.

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance. The issuance of a formal Notice of Allowance at an early date is respectfully requested.

If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 415-576-0200.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

1 1. (Amended) A die seal structure for a semiconductor die having a
2 substrate comprising:
3 an elongate region electrically isolated from the remainder of the substrate
4 extending around a major portion of the periphery of the substrate and having a gap
5 between ends of the elongate region along a minor portion of the periphery; and
6 a conductive seal ring extending around the entire periphery of the die in
7 direct contact with the die [at] throughout said elongate region in direct contact with and
8 said gap to provide a limited electrical connection between the ring and the substrate at
9 said gap.

1 14. (Amended) A die seal structure for a semiconductor die having a
2 substrate of a first conductivity type, comprising:
3 an elongate well region of a second conductivity type opposite from the
4 first conductivity type extending around a major portion of the periphery of the substrate
5 and having a gap between the ends of the elongate region along a minor portion of the
6 periphery; and
7 a conductive seal ring extending around the entire periphery of the die in
8 direct contact with the die [at] throughout said elongate well region and in said gap to
9 provide a limited electrical connection between the ring and the substrate of said first
10 conductivity type at said gap.

1 18. (Amended) A semiconductor device comprising:
2 a. a die including a substrate;
3 b. a die seal structure on the substrate, the structure comprising:
4 an elongate region electrically isolated from the remainder of the
5 substrate extending around a major portion of the periphery of the substrate and having a
6 gap between ends of the elongate region along a minor portion of the periphery; and

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7 a conductive seal ring extending around the entire periphery of the die in
8 direct contact with the die [at] throughout said elongate region and in direct contact with
9 said gap to provide a limited electrical connection between the ring and the substrate at
10 said gap.

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